

 D.G.M.E.	BTA/BTB20CW/BW	版本号: V1. 0
	双向可控硅(三项限) Triacs (3quadrants)	

产品概述 General Description

BTA/BTB20双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，三象限触发，抗干扰能力强，可靠性高。

BTA/BTB20 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

产品特点

MAIN FEATURES

- | | |
|---------------|--|
| ● 表面玻璃钝化，可靠性高 | ● Glass-Passivated Surface For Reliability |
| ● dv/dt高 | ● highly dv/dt |
| ● 通态压降低 | ● Low on-state voltage |
| ● RoHS环保产品 | ● RoHS Products |

应用领域 Applications

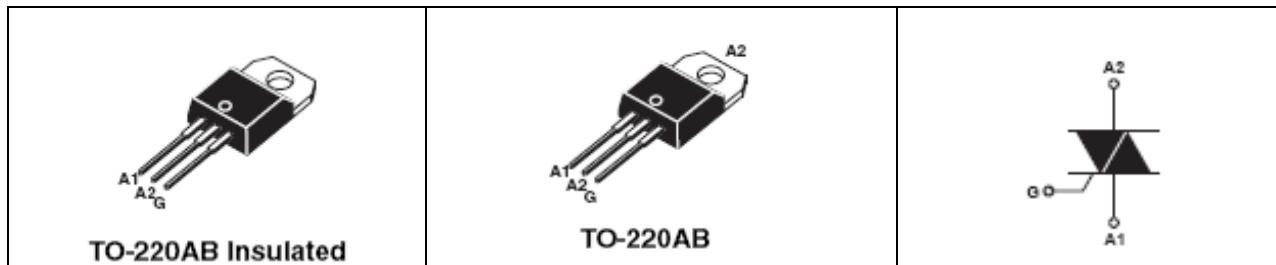
主要应用于调温控制, 调光控制, 调速控制...等。

domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
I _T (RMS)	20	A
V _{DRM} /V _{RRM}	600	V
I _{GT}	50	mA

封装Package: TO-220



极限值(除非另有规定, Ta=25°C) ABSOLUTE RATINGS

(Tj=25°C,unless otherwise specified)

参数 Parameter	符号 symbol	数值 Value	单位 Unit	
RMS 通态电流 on-state RMS current	TO-220ABI _{ns} , T _C =85°C	I _{T(RMS)}	20	
	TO-220AB T _C =100°C			
通态峰值浪涌电流 Non repetitive surge peak on-state current	t=20ms	I _{TSM}	210	A
I ² t 耗散值 I ² t for fusing	T _P =10ms	I ² t	200	A ² s
电流上升率 Repetitive rate of rise of on-state current after triggering	F=120Hz, T _j =125°C	di/dt	50	A/μs
门极峰值电流 Peak gate current		I _{GM}	4	A
平均门极耗散功率 Average gate power		P _{G(AV)}	1.0	W
贮存结温范围 Storage temperature		T _{stg}	-40-+150	°C
工作结温范围 Operation junction temperature		T _j	-40-+125	°C

电参数(除非另有规定, Ta=25°C) ABSOLUTE RATINGS

(Tj=25°C,unless otherwise specified)

参数名称 Parameter	符号 Symbol	测试条件 Test Conditions	规范值 Value		单位 Unit
			CW	BW	
触发电流 Gate trigger current	I _{GT}	V _D =12V, I _T =0.01A	MAX	35	mA
触发电压 Gate trigger voltage	V _{GT}	V _D =12V, I _T =0.01A		1.5	V
维持电流 Holding current	I _H	I _T =500mA		40	mA
电压上升率 Rise of off- state voltage	dv/dt	V _D =67%V _{DRM}	MIN	400	V/μs
通态压降 Peak on-state voltage	V _{TM}	I _T =28A	MAX	1.55	V
断态漏电流 For Peak Repetitive ward Blocking Current	I _{DRM}	V _D =V _{DRM} , T _j =125°C	MAX	1.0	mA

热特性 THERMAL RESISTANCES

参数 Parameter	符号 symbol	数值 Value		单位 Unit
Junction to case(AC)	R _{th(j-lead)}	To-220ABIns.	1.1	°C/W
		TO-220AB	2.0	
Junction to ambient	R _{th(j-a)}	60		°C/W

典型特性曲线ELECTRICAL CHARACTERISTICS(CURVES)

图1 最大耗散功率与RMS通态电流关系
 Fig.1. Maximum Power Dissipation Versus on-state current

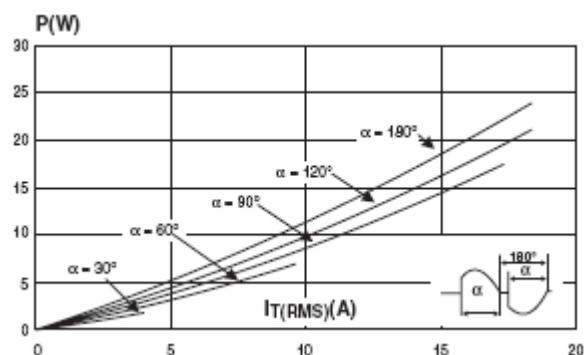


图2 平均通态电流与 T_c 温度关系
 Fig.2. On-state Current Versus T_c

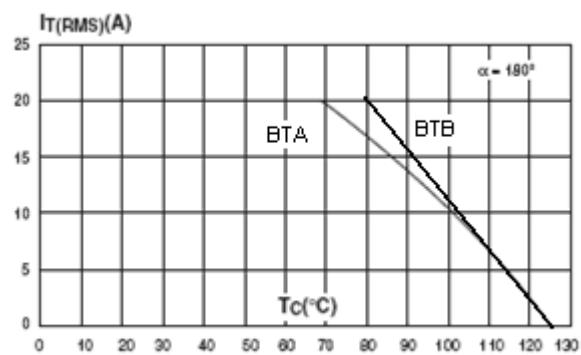


图3 通态特性
 Fig.3. On-State Characteristics

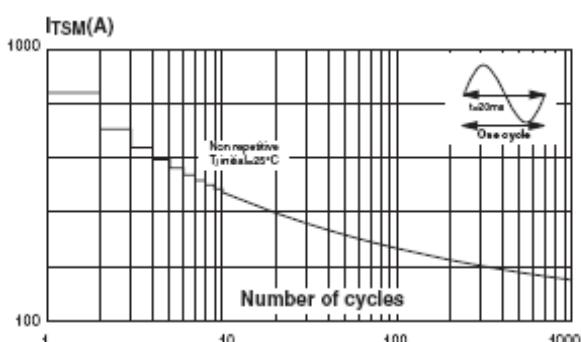


图4 通态浪涌峰值电流与周期数关系
 Fig.4. Surge Peak On-state Current Versus Number Cycles

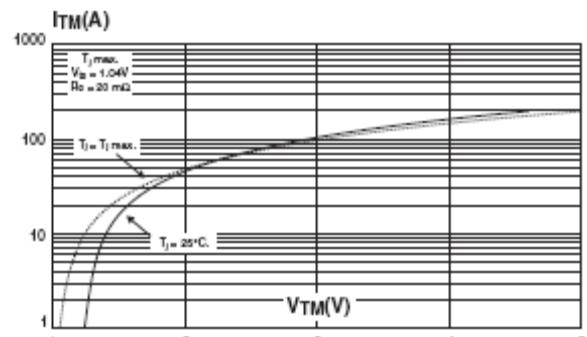
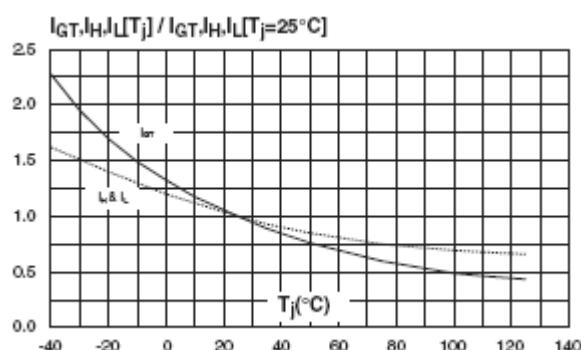
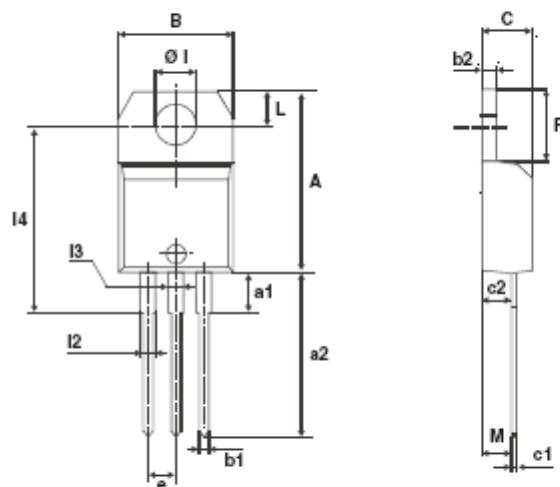


图5 I_{GT} 、 I_H 、 I_L 相对值（相对于25°C）与结温关系
 Fig.5. Relative Variation Of Gate Trigger Current Holding Current And Latching Current Versus Junction Temperature (Typical Value)



TO-220AB外形图 Package Mechanical Data



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.40		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
Ø1	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	